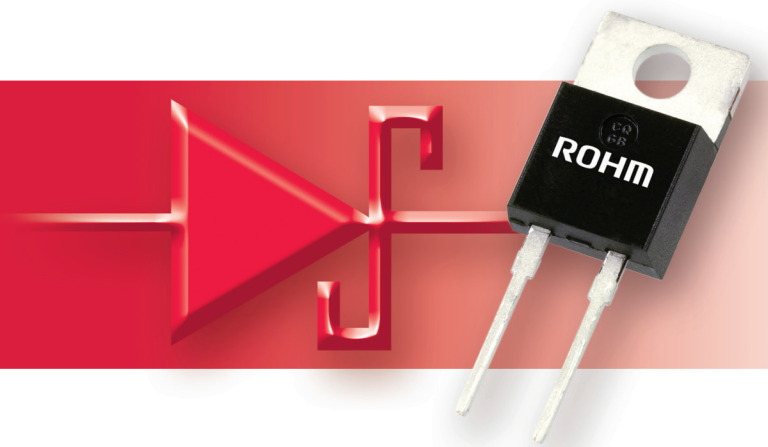




*Innovations Embedded*

# Silicon Carbide Schottky Barrier Diodes



## Choosing Silicon Carbide Instead of Silicon

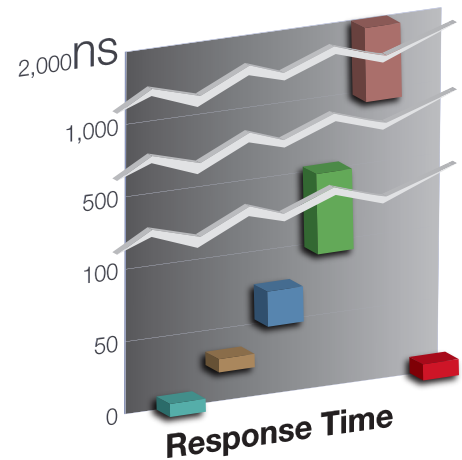
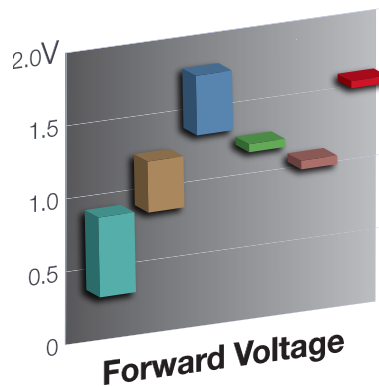
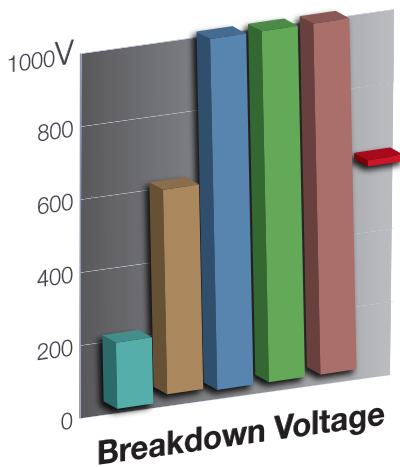
Schottky barrier diodes (SBDs) have the advantage of low forward losses and negligible switching losses compared to other diode technologies. But the narrow bandgap of silicon (Si) SBDs limits their use to a maximum voltage of around 200 V. Si diodes that operate above 200 V have higher  $V_F$  and  $t_{rr}$ .

Silicon carbide (SiC) is a compound semiconductor with superior power characteristics to silicon, including a bandgap approximately three times greater, a dielectric breakdown

field 10 times higher, and a thermal coefficient three times larger. These characteristics make it ideal for power electronics applications.

Today, the need for higher efficiency in end products is more critical than ever. Although silicon power products continue to see incremental improvements, devices based on compound semiconductor materials deliver significantly better performance — and in some cases not even possible with their silicon counterparts.

This is certainly true for the most basic components in power electronics: diodes and transistors. Silicon carbide Schottky barrier diodes have been available for more than a decade but have not been commercially viable until recently. Volume production is now leading to SiC's acceptance in more and more applications.



### Legend

- Si Schottky Barrier Diode
- Si Super Fast Diode
- Si Ultra Fast Diode
- Si Fast Recovery (Epitaxial) Diode
- Si Standard Recovery Diode
- Silicon Carbide Schottky Barrier Diode

## 600V Diodes

### ■ SCS106AGC, SCS108AGC, SCS110AGC, SCS112AGC, and SCS120AGC

The SCS1xxAGC series of 600 V silicon carbide Schottky barrier diodes offers industry-leading low forward voltage and fast recovery time. They maintain low forward voltage ( $V_F$ ) over a wide operating temperature range which results in lower power

dissipation under actual operating conditions. Low  $V_F$  minimizes switching loss and enables high switching frequency, resulting in smaller passives and smaller end-product form factors.

### Applications

- Power Factor Correction / SMPS
- Solar Inverters
- Motor Drives

### Important Features / Advantages

- Extremely low switching loss
- Excellent thermal conductivity and high operating temperature eliminates or greatly reduces heat sink requirements
- Reduced EMI emission

## DESIGN NOTE

**With an SiC Schottky barrier diode (SBD), switching losses are reduced by 2/3 compared to a silicon fast recovery diode (FRD). (The Si FRD is used for comparison since it has a comparable voltage rating to the SiC SBD.)**

## SiC Performance Improvement over Si FRD

The graph plots Current (A) on the y-axis (from -5 to 2) against Time (nsec) on the x-axis (from 50 to 125). Two curves are shown: a red curve for SiC SBD and a blue curve for Si FRD. Both show a negative current pulse during switching. The SiC SBD pulse is significantly narrower and shallower than the Si FRD pulse. A red callout box with a speech bubble points to the SiC SBD pulse, stating 'Switching losses reduced by 2/3'. The Si FRD pulse is shaded with a blue grid pattern. The area under the SiC SBD pulse is shaded with a red grid pattern. The reverse recovery time  $t_{rr}$  is indicated for both curves.

Part No.	Reverse voltage (V) $V_{RM}$	Continuous forward current (A) $I_F$	Forward voltage (V)		Reverse current ( $\mu A$ )		Total power dissipation (W) $P_d$	Capacitive charge (nC) $Q_c$	Switching time (ns) $t_c$	Total capacitance (pF) C $V_s = 1V/V_s = 600V$	Thermal resistance ( $^{\circ}C/W$ ) $R_{th(j-c)}$	Package
			$V_{RM}$ (typ)	$V_{RM}$ (max)	$I_R$ (typ)	$I_R$ (max)						
			$T_J = 25^{\circ}C/150^{\circ}C$		$T_J = 25^{\circ}C/150^{\circ}C$							
SCS106AGC	600	6	1.5/1.6	1.7	1.2/6	120	48	12	18	260/28	2.6	TO220AC 2L
SCS108AGC	600	8	1.5/1.6	1.7	1.6/8	160	52	15	15	345/38	2.4	TO220AC 2L
SCS110AGC	600	10	1.5/1.6	1.7	2.0/10	200	57	16	15	430/47	2.2	TO220AC 2L
SCS112AGC	600	12	1.5/1.6	1.7	2.4/12	240	80	22	16	516/56	1.6	TO220AC 2L
SCS120AGC	600	20	1.5/1.6	1.7	4.0/20	400	97	35	19	860/93	1.3	TO220AC 2L



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